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Application Number	10/813,233
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First Named Inventor	Shunpei YAMAZAKI et al.
Art Unit	2823
Examiner Name	Trung Q. Dang
Attorney Docket Number	740756-2719

**U.S. PATENT DOCUMENTS**

Examiner Initials <sup>1</sup>	Cite No. <sup>2</sup>	U.S. Patent Document Number - Kind Code <sup>3</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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**OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS**

Examiner Initials <sup>1</sup>	Cite No. <sup>2</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>
T. D		H. HAYASHI et al., "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method", IEDM 95: Technical Digest of International Electronic Devices Meeting, 1995 IEEE, pgs. 33.3.1-4 (pgs. 829-832).	

Examiner Signature	T. DANG	Date Considered	6/24/05
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